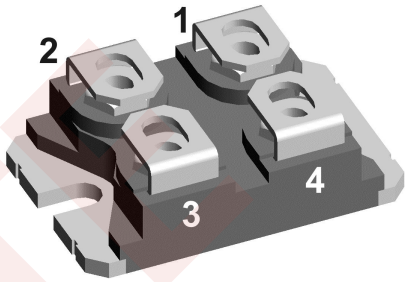
FRED

V_{RRM}	=	1200 V
I_{FAV}	= 2x	99 A
t_{rr}	=	40 ns

Fast Recovery Epitaxial Diode
Low Loss and Soft Recovery
Parallel legs

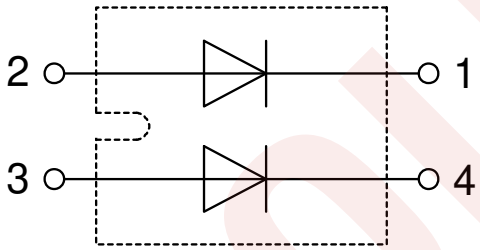
Part number

DSEI2x101-12A



Backside: isolated

E72873



Features / Advantages:

- Planar passivated chips
- Low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

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Fast Diode

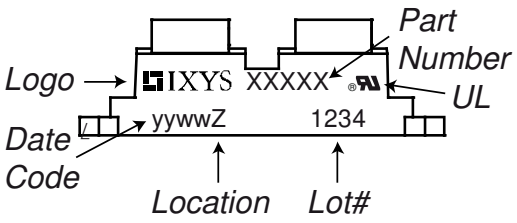
Symbol	Definition	Conditions		Ratings min.	typ.	max.	Unit
V_{RSM}	*max. non-repetitive reverse blocking voltage*		T_{VJ} = 25°C			1200	V
V_{RRM}	*max. repetitive reverse blocking voltage*		T_{VJ} = 25°C			1200	V
I_R	*reverse current, drain current*	V_R = 1200 V	T_{VJ} = 25°C			3	mA
		V_R = 960 V	T_{VJ} = 125°C			15	mA
V_F	*forward voltage drop*	I_F = 100 A	T_{VJ} = 25°C			1.87	V
		I_F = 200 A				2.13	V
		I_F = 100 A	T_{VJ} = 150°C			1.61	V
		I_F = 200 A				1.92	V
I_{FAV}	*average forward current*	T_C = 50°C	T_{VJ} = 150°C			99	A
		rectangular d = 0.5					
V_{F0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 150°C			1.01	V
r_F	*slope resistance* }					6.1	mΩ
R_{thJC}	*thermal resistance junction to case*					0.5	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.10		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			250	W
I_{FSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine; V_R = 0 V	T_{VJ} = 45°C			900	A
C_J	*junction capacitance*	V_R = 400 V f = 1 MHz	T_{VJ} = 25°C		107		pF
I_{RM}	*max. reverse recovery current*		T_{VJ} = 25 °C		38		A
		I_F = 100 A; V_R = 600 V	T_{VJ} = 100 °C		52		A
t_{rr}	*reverse recovery time*	$-di_F/dt$ = 600 A/µs	T_{VJ} = 25 °C		150		ns
			T_{VJ} = 100 °C		255		ns

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Package SOT-227B (minibloc)					Ratings			
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I_{RMS}	*RMS current*	per terminal					150	A
T_{VJ}	*virtual junction temperature*				-40		150	°C
T_{op}	*operation temperature*				-40		125	°C
T_{stg}	*storage temperature*				-40		150	°C
Weight						30		g
M_D	*mounting torque*				1.1		1.5	Nm
M_T	*terminal torque*				1.1		1.5	Nm
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*		*terminal to terminal*	10.5	3.2			mm
$d_{Spb/Apb}$			*terminal to backside*	8.6	6.8			mm
V_{ISOL}	*isolation voltage*	t = 1 second	50/60 Hz, RMS; I_{ISOL} ≤ 1 mA		3000			V
		t = 1 minute			2500			V

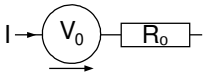
Product Marking



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEI2x101-12A	DSEI2x101-12A	Tube	10	468002

Equivalent Circuits for Simulation

** on die level* T_{VJ} = 150 °C

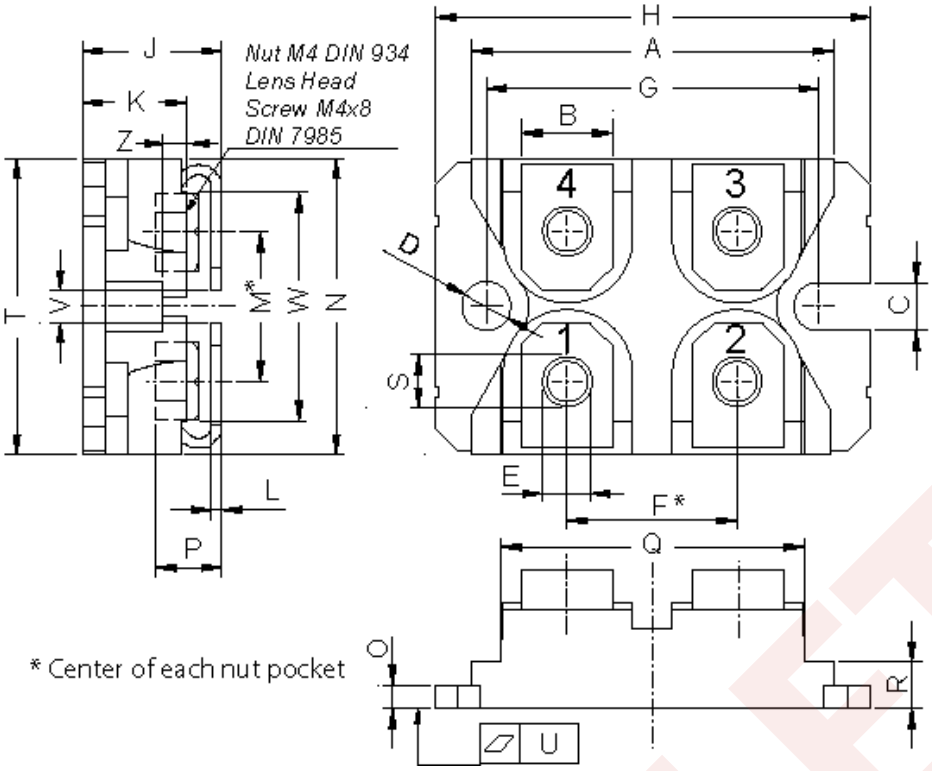


		Fast Diode	
$V_{0\,max}$	*threshold voltage*	1.01	V
$R_{0\,max}$	*slope resistance **	4.9	mΩ

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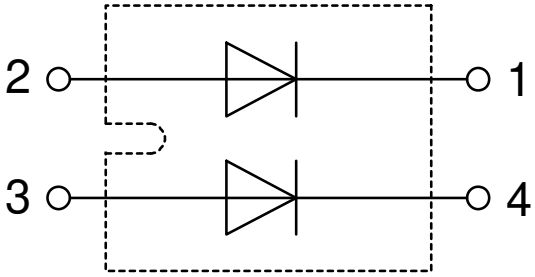
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Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106

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Fast Diode

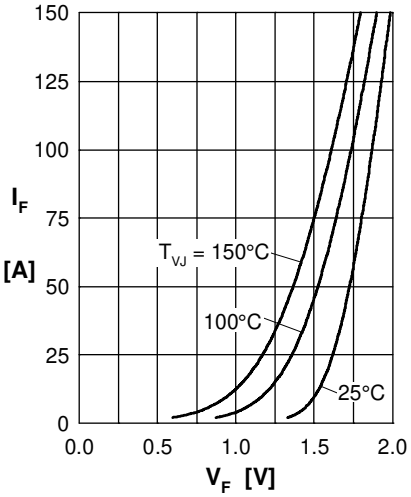


Fig. 1 Forward current I_F versus V_F

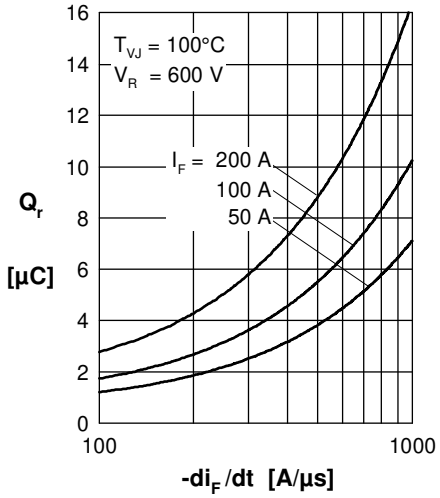


Fig. 2 Typ. reverse recov. charge Q_{rr} versus $-di_F/dt$

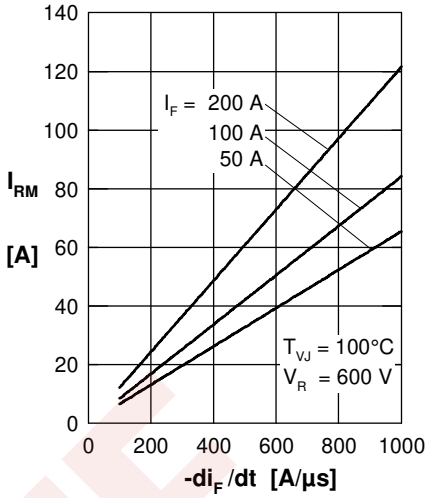


Fig. 3 Typ. peak reverse current I_{rr} versus $-di_F/dt$

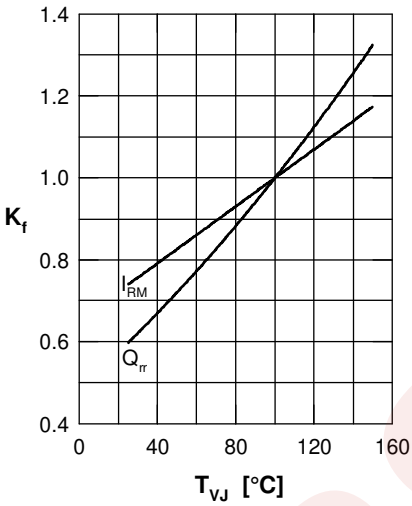


Fig. 4 Dyn. parameters Q_r, I_{RM} versus T_{VJ}

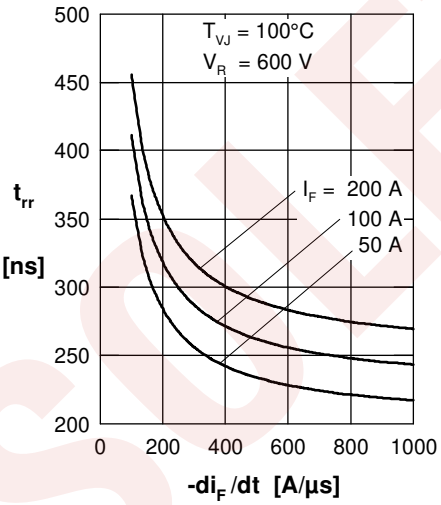


Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

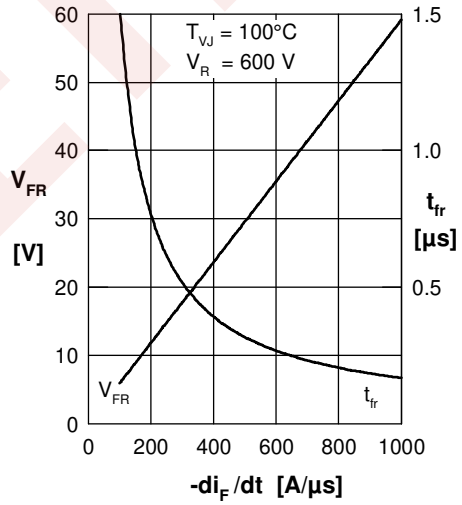


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt

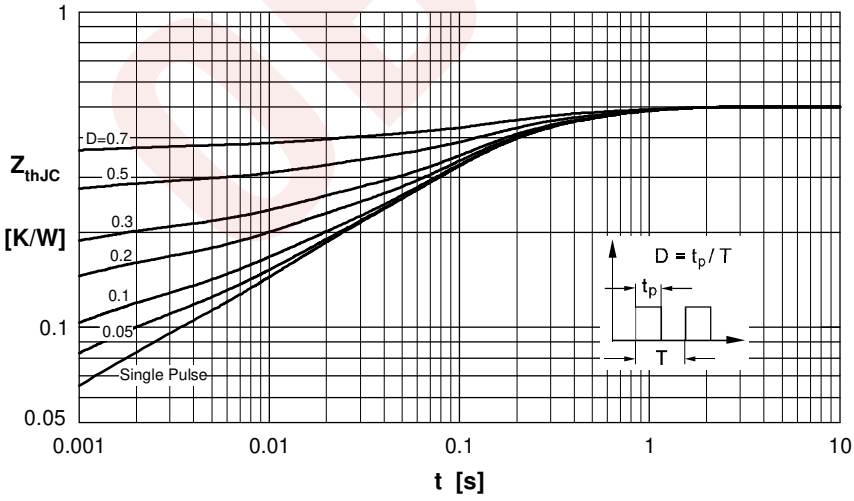


Fig. 7 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.020	0.00002
2	0.050	0.00081
3	0.076	0.01000
4	0.240	0.09400
5	0.114	0.45000

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